

SMB1N-770D

- IR High-Power LED
- 770 nm, 650 mW
- AlGaInP chip, 1000 x 1000 μm
- PA9T SMD package
- Beam Angle: ± 64°



Description



SMB1N-770D is a surface mount AlGaInP based high power infrared LED, with a typical peak wavelength of 770 nm and optical output power of 650 mW @ 800 mA. It comes in polyamide resin SMD package (PA9T) with silver plated soldering pads (lead free solderable), copper heat sink, and silicone resin mold. Additional variants with different beam angles are available on request.

Maximum Ratings*

Doubleston	Cumbal	Va	I I m i d		
Parameter	Symbol	Min.	Max.	Unit	
Power Dissipation	PD		2000	mW	
Forward Current	lF		800	mA	
Pulse Forward Current **	I FP		2000	mA	
Reverse Voltage (I _R =10 μA)	U R		5	V	
Reverse Current (U _R =5 V)	I _R		10	μΑ	
Thermal Resistance	RTHJA		10	K/W	
Junction Temperature	TJ		120	°C	
Operating Temperature	TCASE	- 40	+ 100	°C	
Storage Temperature	T _{STG}	- 40	+ 100	°C	
Lead Solder Temperature (t _{max} . 5s)	T _{SLD}		+ 250	°C	

^{*}Operating close to or exceeding these parameters may damage the device

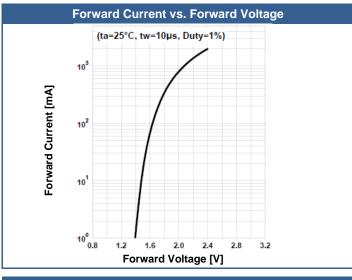
Electro-Optical Characteristics (TCASE = 25°C)

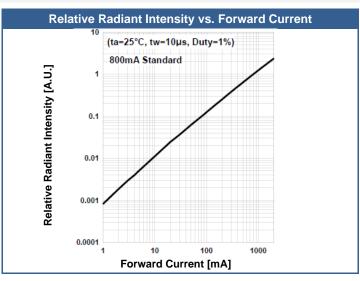
Parameter	Symbol	Conditions	Min.	Values Typ.	Max.	Unit
Peak Wavelength	λ_P	I _F =800 mA	760		780	nm
Half Width	λ_{Δ}	I _F =800 mA		20		nm
Forward Voltage	UF	I _F =800 mA		2.1	2.5	V
	U_{FP}	I _{FP} =2 A		2.6		
Total Radiated Power	Po	I _F =800 mA	450	650		mW
		I _{FP} =2 A		1500		
Radiant Intensity	lE	I _F =800 mA		180		mW/sr
		I _{FP} =2 A		430		
Viewing Angle	2θ _{1/2}	I _F =100 mA		128		deg.
Rise Time	t _r	I _F =800 mA		45		ns
Fall Time	t f	I _F =800 mA		40		ns

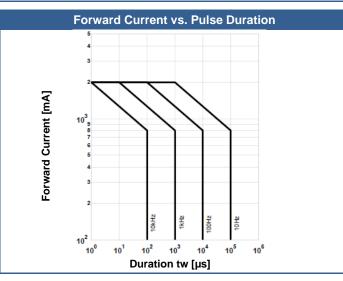
^{*} duty cycle = 1 %, pulse width = 10 μs

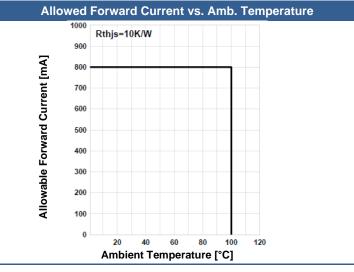
^{**} duty cycle = 1 %, pulse width = 10 μ s

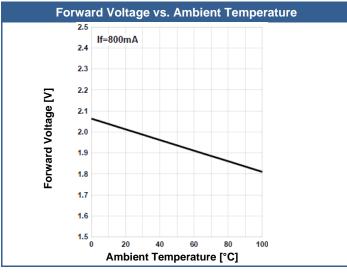
Typical Performance Curves

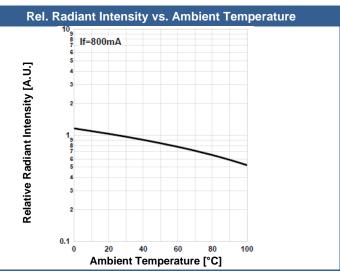






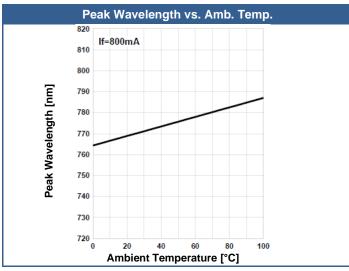


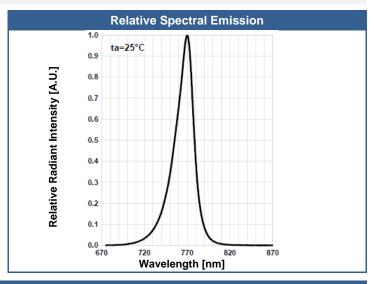


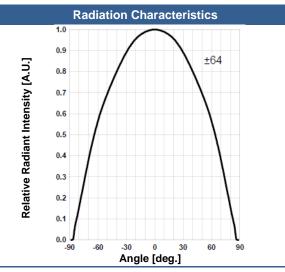


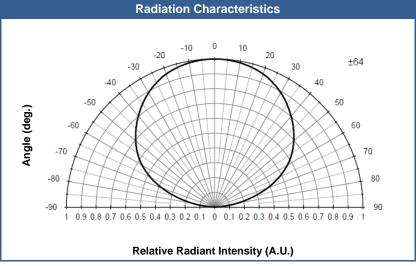


Typical Performance Curves

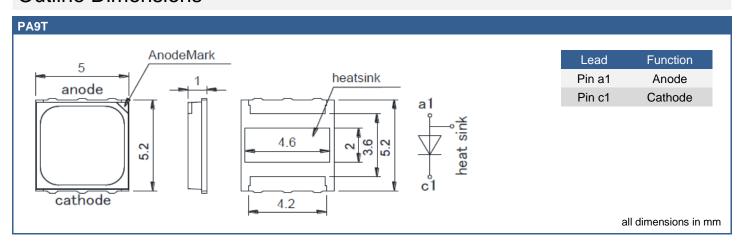








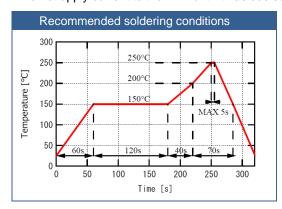
Outline Dimensions

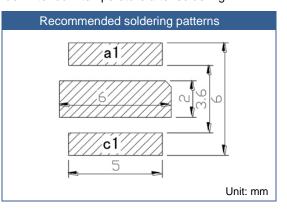


General Notes

Soldering

- · Do avoid overheating of the LED
- Do avoid electrostatic discharge (ESD)
- Do avoid mechanical stress, shock, and vibration
- Do only use non-corrosive flux
- . Do not apply current to the LED until it has cooled down to room temperature after soldering





Cleaning

- . Cleaning with isopropyl alcohol, propanol, or ethyl alcohol is recommended
- DO NOT USE acetone, chloroseen, trichloroethylene, or MKS
- DO NOT USE ultrasonic cleaners

Static Electricity

- LEDs are sensitive to electrostatic discharge (ESD).
- Precautions against ESD must be taken when handling or operating these LEDs
- Surge voltage or electrostatic discharge can result in complete failure of the LED.

Radiation

- During operation these LEDs do emit light, which could be hazardous to skin and eyes, and may cause cancer.
- · Do avoid exposure to the emitted light. Protective glasses if needed
- It is further advised to attach a warning label on products/systems.

Operation

- · Do only operate LEDs with a current source.
- Running these LEDs from a voltage source will result in complete failure of the device.
- Current of a LED is an exponential function of the voltage across it. Usage of current regulated drive circuits is mandatory.

Storage

- The maximum shelf life of LEDs in the originally sealed aluminum bag is 12 months.
- Before opening the aluminum bag, please store it at <30 °C, <60 % RH.
- After opening the aluminum bag, please solder the LEDs within 72 hours (floor life) at 5 − 30 °C, <50 % RH.
- Put any unused, remaining LEDs and silica gel back in the same aluminum bag and then vacuum-seal the bag.
- It is recommended to keep the re-sealed bag in a desiccator at <30%RH.

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The above specifications are for reference purpose only and subjected to change without prior notice